

**RADIATION HARDENED  
 POWER MOSFET  
 SURFACE MOUNT (SMD-2)**

**IRHNA7260  
 200V, N-CHANNEL  
 REF: MIL-PRF-19500/664  
 RAD-Hard™ HEXFET®  
 MOSFET TECHNOLOGY**

**Product Summary**

Part Number	Radiation Level	RDS(on)	Id	QPL Part Number
IRHNA7260	100K Rads (Si)	0.07Ω	43A	JANSR2N7433U
IRHNA3260	300K Rads (Si)	0.07Ω	43A	JANSF2N7433U
IRHNA4260	600K Rads (Si)	0.07Ω	43A	JANSG2N7433U
IRHNA8260	1000K Rads (Si)	0.07Ω	43A	JANSH2N7433U



International Rectifier's RADHard HEXFET® technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low Rds(on) and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

**Features:**

- Single Event Effect (SEE) Hardened
- Low RDS(on)
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Light Weight

**Absolute Maximum Ratings**

**Pre-Irradiation**

	Parameter		Units
Id @ VGS = 12V, TC = 25°C	Continuous Drain Current	43	A
Id @ VGS = 12V, TC = 100°C	Continuous Drain Current	27	
IDM	Pulsed Drain Current ①	172	
PD @ TC = 25°C	Max. Power Dissipation	300	W
	Linear Derating Factor	2.4	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	500	mJ
IAR	Avalanche Current ①	43	A
EAR	Repetitive Avalanche Energy ①	30	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.7	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Pckg. Mounting Surface Temp.	300 ( for 5s)	
	Weight	3.3 (Typical)	g

For footnotes refer to the last page

**Electrical Characteristics @ T<sub>j</sub> = 25°C (Unless Otherwise Specified)**

	Parameter	Min	Typ	Max	Units	Test Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	200	—	—	V	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1.0mA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	—	0.26	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1.0mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-State Resistance	—	—	0.070	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> = 27A
		—	—	0.077		V <sub>GS</sub> = 12V, I <sub>D</sub> = 43A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1.0mA
g <sub>fs</sub>	Forward Transconductance	9.0	—	—	S (r <sub>s</sub> )	V <sub>DS</sub> > 15V, I <sub>DS</sub> = 27A ④
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	—	25	μA	V <sub>DS</sub> = 160V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 160V V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	—	100	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	—	290	nC	V <sub>GS</sub> = 12V, I <sub>D</sub> = 43A V <sub>DS</sub> = 100V
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	42		
Q <sub>gd</sub>	Gate-to-Drain ('Miller') Charge	—	—	120		
t <sub>d(on)</sub>	Turn-On Delay Time	—	—	50	ns	V <sub>DD</sub> = 100V, I <sub>D</sub> = 43A, R <sub>G</sub> = 2.35Ω
t <sub>r</sub>	Rise Time	—	—	200		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	—	200		
t <sub>f</sub>	Fall Time	—	—	130		
L <sub>S</sub> + L <sub>D</sub>	Total Inductance	—	4.0	—	nH	Measured from center of drain pad to center of source pad
C <sub>iss</sub>	Input Capacitance	—	5300	—	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	1200	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	360	—		

**Source-Drain Diode Ratings and Characteristics**

	Parameter	Min	Typ	Max	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	43	A	T <sub>j</sub> = 25°C, I <sub>S</sub> = 43A, V <sub>GS</sub> = 0V ④
I <sub>SM</sub>	Pulse Source Current (Body Diode) ①	—	—	172		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.8	V	T <sub>j</sub> = 25°C, I <sub>F</sub> = 43A, di/dt ≥ 100A/μs
t <sub>rr</sub>	Reverse Recovery Time	—	—	820	nS	V <sub>DD</sub> ≤ 25V ④
Q <sub>RR</sub>	Reverse Recovery Charge	—	—	8.5	μC	
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L <sub>S</sub> + L <sub>D</sub> .				

**Thermal Resistance**

	Parameter	Min	Typ	Max	Units	Test Conditions
R <sub>thJC</sub>	Junction-to-Case	—	—	0.42	°C/W	Solder to a 1" sq. copper clad PC Board
R <sub>thJPCB</sub>	Junction-to-PC Board	—	1.6	—		

Note: Corresponding Spice and Saber models are available on the G&S Website.

For footnotes refer to the last page

## Radiation Characteristics

IRHNA7260

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

**Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥**

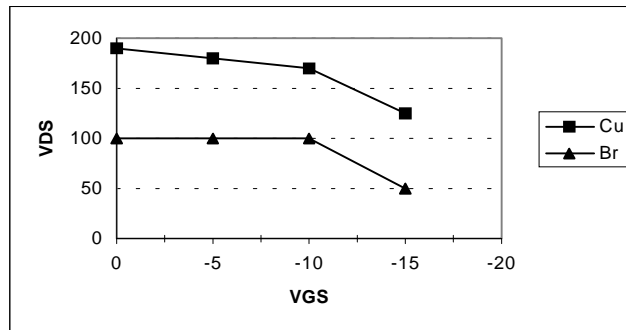
	Parameter	100K Rads(Si) <sup>1</sup>		600 to 1000K Rads (Si) <sup>2</sup>		Units	Test Conditions
		Min	Max	Min	Max		
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	200	—	200	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
V <sub>GS(th)</sub>	Gate Threshold Voltage ④	2.0	4.0	1.25	4.5		V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 1.0mA
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	100	—	100	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	-100	—	-100		V <sub>GS</sub> = -20V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	25	—	50	μA	V <sub>DS</sub> =160V, V <sub>GS</sub> =0V
R <sub>DS(on)</sub>	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.075	—	0.16	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> =27A
R <sub>DS(on)</sub>	Static Drain-to-Source ④ On-State Resistance (SMD-2)	—	0.07	—	0.11	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> =27A
V <sub>SD</sub>	Diode Forward Voltage ④	—	1.8	—	1.8	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 43A

1. Part number IRHNA7260 (JANSR2N7433U)

2. Part numbers IRHNA3260 (JANSF2N7433U), IRHNA4260 (JANSJ2N7433U) and IRHNA8260 (JANSH2N7433U)

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Ion	LET MeV/(mg/cm <sup>2</sup> )	Energy (MeV)	Range (μm)	V <sub>DS</sub> (V)				
				@V <sub>GS</sub> =0V	@V <sub>GS</sub> =-5V	@V <sub>GS</sub> =-10V	@V <sub>GS</sub> =-15V	@V <sub>GS</sub> =-20V
Cu	28	285	43	190	180	170	125	—
Br	36.8	305	39	100	100	100	50	—



**Fig a. Single Event Effect, Safe Operating Area**

For footnotes refer to the last page

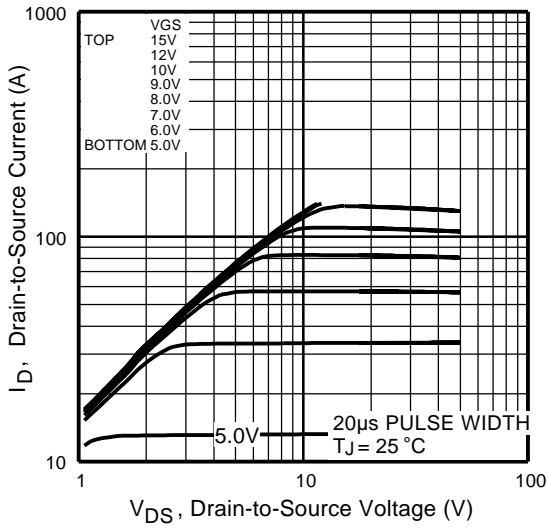


Fig 1. Typical Output Characteristics

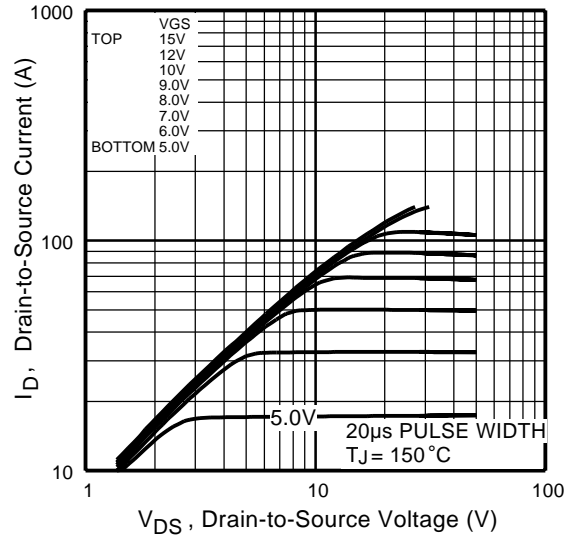


Fig 2. Typical Output Characteristics

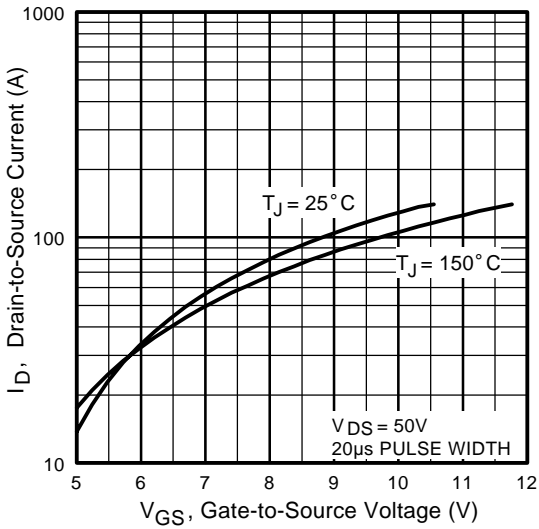


Fig 3. Typical Transfer Characteristics

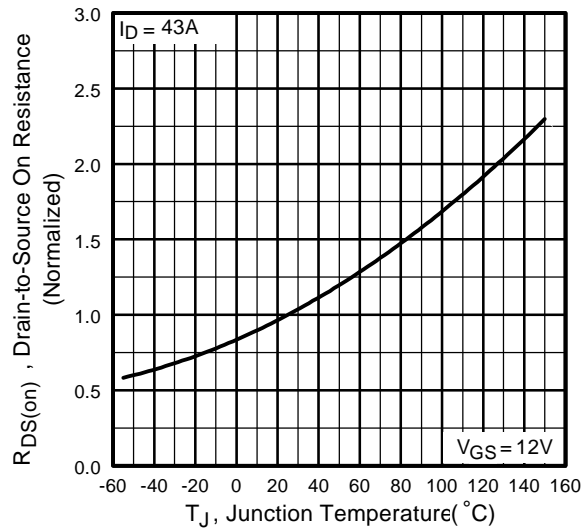


Fig 4. Normalized On-Resistance Vs. Temperature

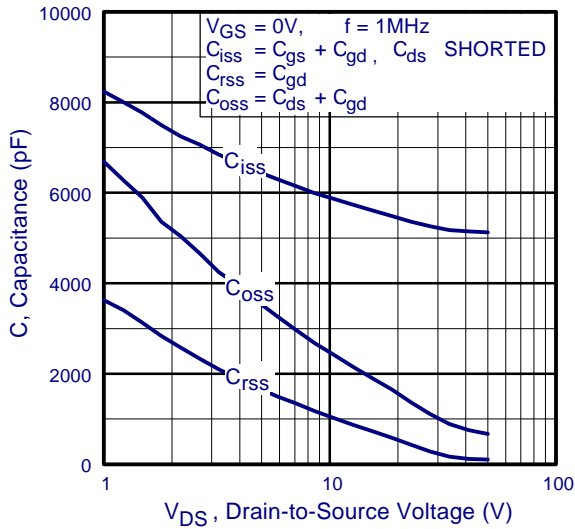


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

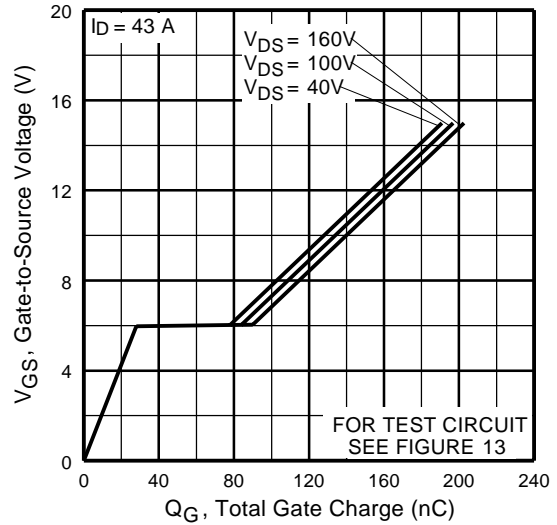


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

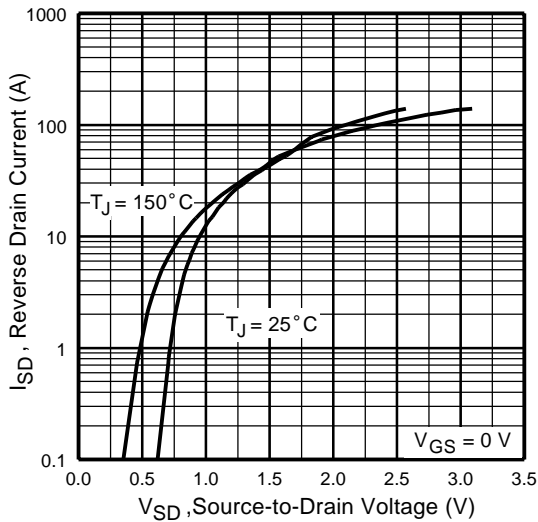


Fig 7. Typical Source-Drain Diode Forward Voltage

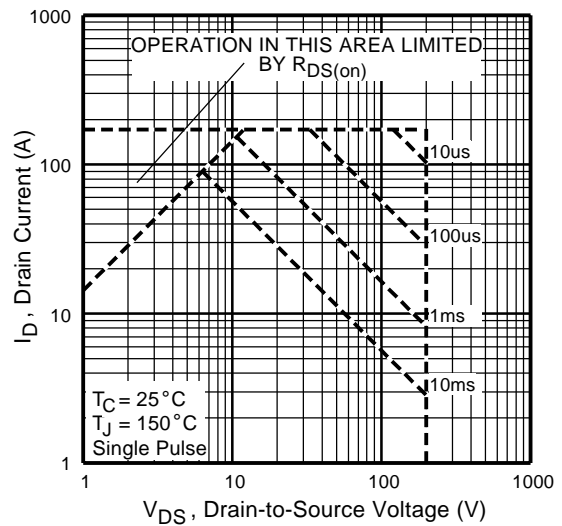


Fig 8. Maximum Safe Operating Area

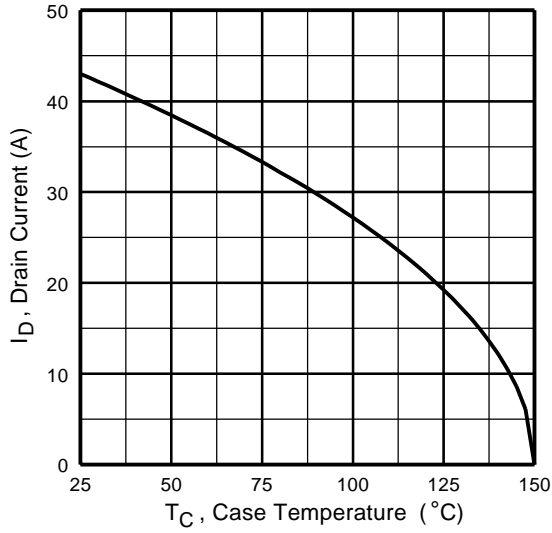


Fig 9. Maximum Drain Current Vs. Case Temperature

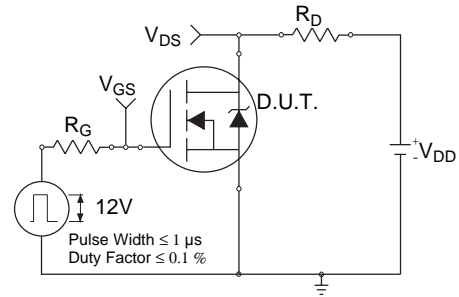


Fig 10a. Switching Time Test Circuit

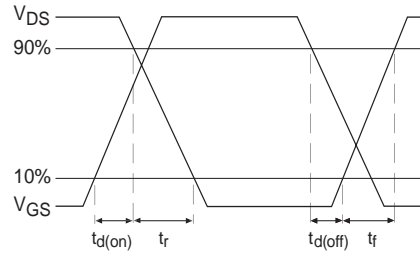


Fig 10b. Switching Time Waveforms

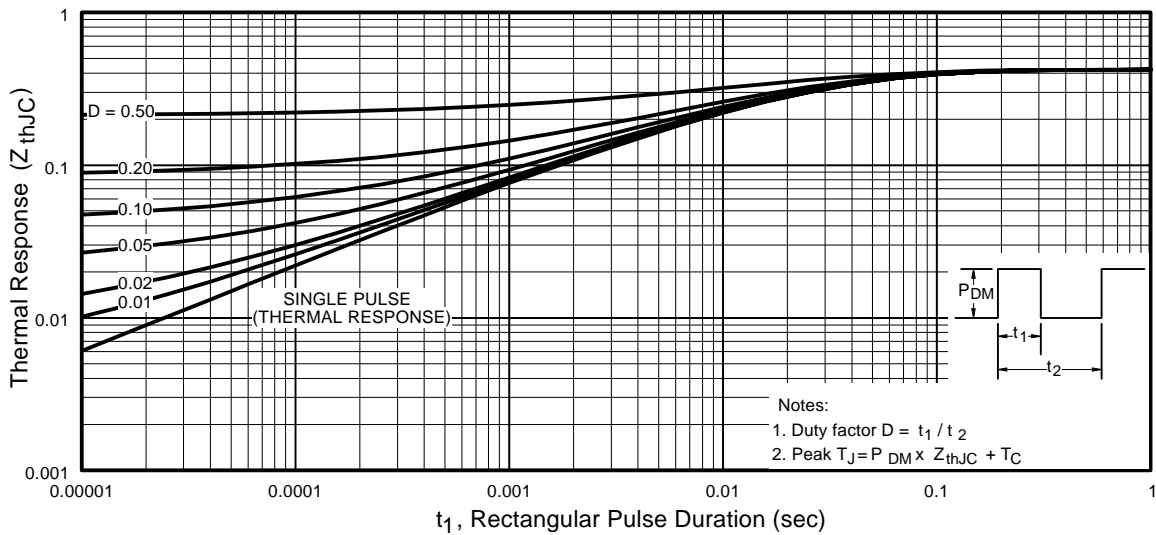


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

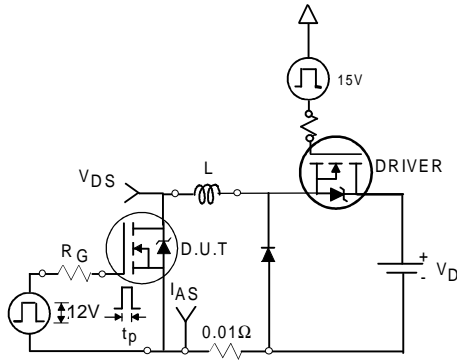


Fig 12a. Unclamped Inductive Test Circuit

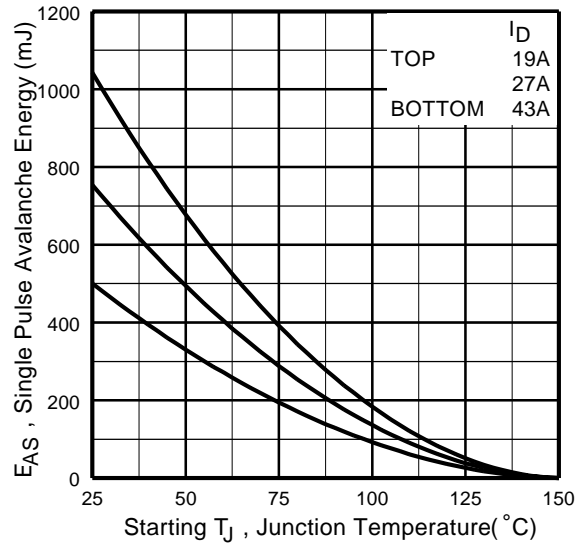


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

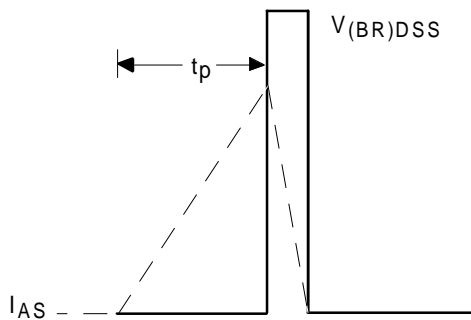


Fig 12b. Unclamped Inductive Waveforms

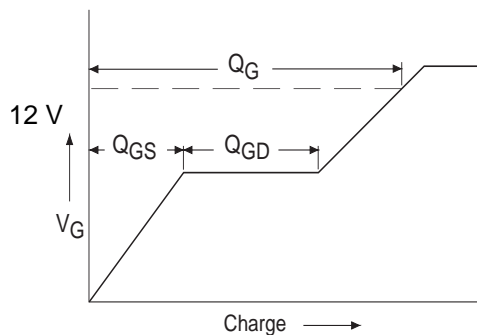


Fig 13a. Basic Gate Charge Waveform

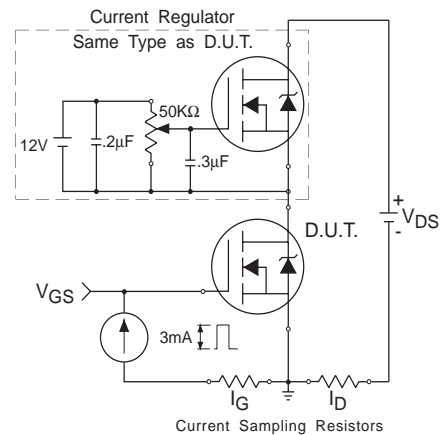
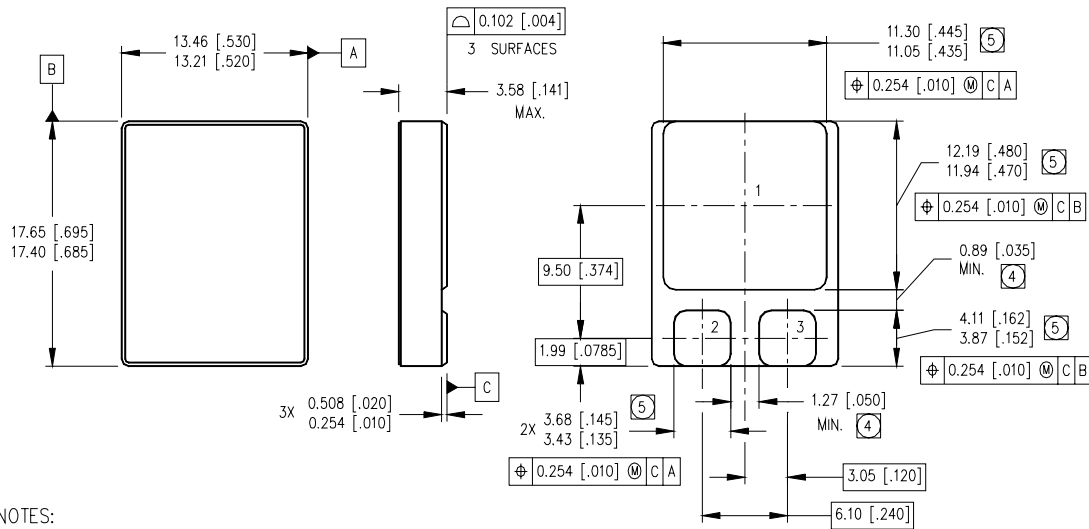


Fig 13b. Gate Charge Test Circuit

**Foot Notes:**

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ②  $V_{DD} = 25V$ , starting  $T_J = 25^\circ C$ ,  $L = 0.54mH$   
Peak  $I_L = 43A$ ,  $V_{GS} = 12V$
- ③  $I_{SD} \leq 43A$ ,  $di/dt \leq 410A/\mu s$ ,  
 $V_{DD} \leq 200V$ ,  $T_J \leq 150^\circ C$
- ④ Pulse width  $\leq 300 \mu s$ ; Duty Cycle  $\leq 2\%$
- ⑤ **Total Dose Irradiation with  $V_{GS}$  Bias.**  
12 volt  $V_{GS}$  applied and  $V_{DS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with  $V_{DS}$  Bias.**  
160 volt  $V_{DS}$  applied and  $V_{GS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.

**Case Outline and Dimensions — SMD-2**



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- ④ DIMENSION INCLUDES METALLIZATION FLASH.
- ⑤ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

- 1 = DRAIN
- 2 = GATE
- 3 = SOURCE

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
**IR EUROPEAN REGIONAL CENTRE:** 439/445 Godstone Rd, Whyteleafe, Surrey CR3 OBL, UK Tel: ++ 44 (0)20 8645 8000  
**IR CANADA:** 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200  
**IR GERMANY:** Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590  
**IR ITALY:** Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111  
**IR JAPAN:** K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086  
**IR SOUTHEAST ASIA:** 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 (0)838 4630  
**IR TAIWAN:** 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673 Tel: 886-(0)2 2377 9936  
*Data and specifications subject to change without notice. 5/00*